

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

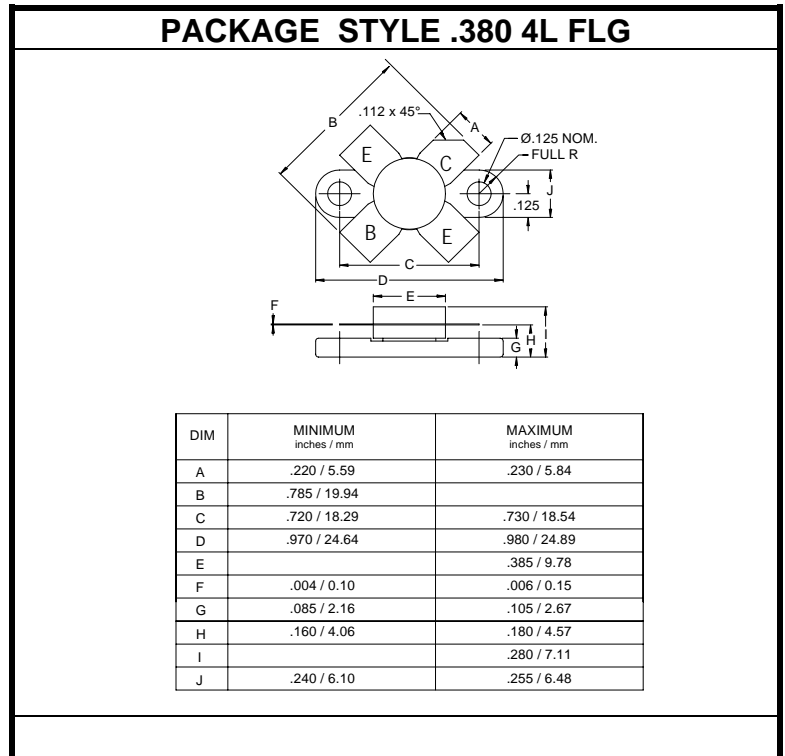
The **ASI MRF466** is Designed for power amplifier applications from 2.0 to 30MHz.

**FEATURES:**

- $P_G = 15$  dB min. at 40 W/30 MHz
- $IMD_3 = -30$  dBc max. at 40 W (PEP)
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	6.0 A
$V_{CBO}$	65 V
$V_{CEO}$	35 V
$P_{DISS}$	175 W @ $T_C = 25^\circ C$
$T_J$	-65 °C to +200 °C
$T_{STG}$	-65 °C to +150 °C
$\theta_{JC}$	1.0 °C/W


**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 100$ mA	35			V
$BV_{CES}$	$I_C = 100$ mA	65			V
$BV_{EBO}$	$I_E = 1.0$ mA	4.0			V
$I_{CES}$	$V_E = 28$ V			5	mA
$h_{FE}$	$V_{CE} = 5.0$ V $I_C = 0.5$ A	10		80	---
$C_{ob}$	$V_{CB} = 28$ V $f = 1.0$ MHz		125	200	pF
$G_{PE}$	$V_{CE} = 28$ V $I_{CQ} = 20$ mA $f = 30$ MHz	15	19		dB
$\eta$	$P_{OUT} = 40$ W (PEP)	40			%
$IMD_3$			-40	-30	dBc